

**SANYO**

P-Channel MOS Silicon FET

## Very High-Speed Switching Applications

**Features**

- Low ON resistance
- Very high-speed switching
- Low-voltage drive

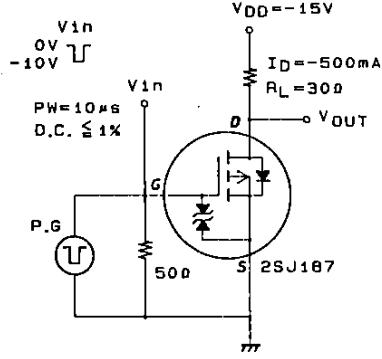
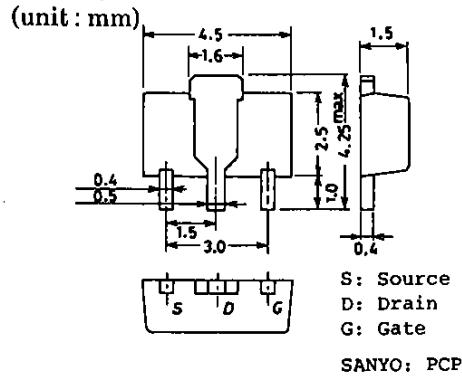
**Absolute Maximum Ratings at Ta = 25°C**

Drain to Source Voltage	V <sub>DSS</sub>	-30	V
Gate to Source Voltage	V <sub>GSS</sub>	±15	V
Drain Current (DC)	I <sub>D</sub>	-1	A
Drain Current (Pulse)	I <sub>DP</sub>	PW ≤ 10 μs, duty cycle ≤ 1%	-4 A
Allowable Power Dissipation	P <sub>D</sub>	T <sub>c</sub> = 25°C Mounted on ceramic board (250mm <sup>2</sup> × 0.8mm)	3.5 W 1.5 W
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>tsg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

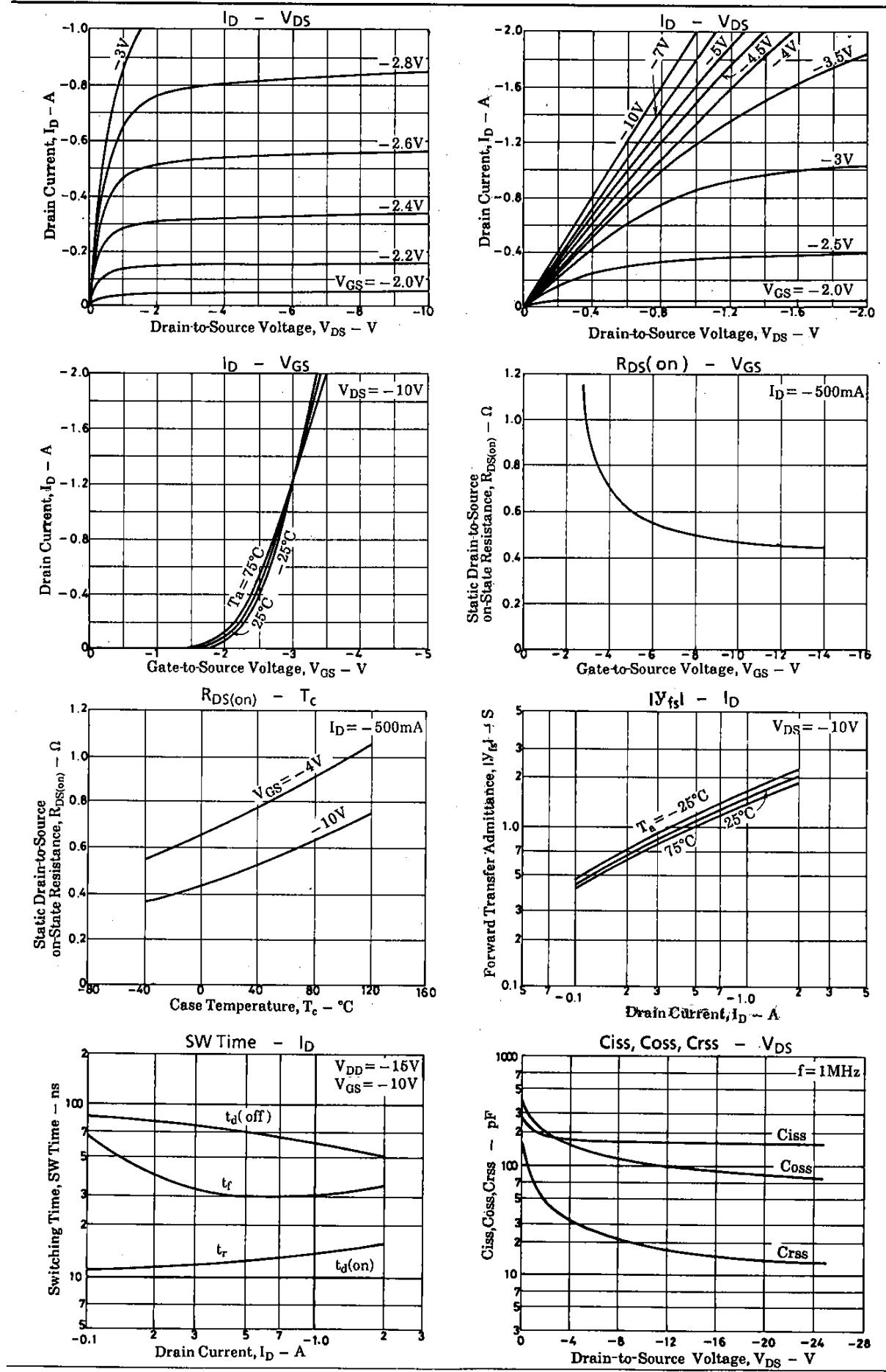
			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0	-30			V
[Zero Gate Voltage Drain Current]	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0			-100	μA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -500mA	0.6	1.0		S
[Static Drain to Source on State Resistance]	R <sub>DS(on)</sub>	I <sub>D</sub> = -500mA, V <sub>GS</sub> = -10V	0.5	0.75		Ω
Input Capacitance	C <sub>iss</sub>	I <sub>D</sub> = -500mA, V <sub>GS</sub> = -4V	0.75	1.1		Ω
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10V, f = 1MHz	170			pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -10V, f = 1MHz	110			pF
Turn-ON Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = -10V, f = 1MHz	20			pF
Rise Time	t <sub>r</sub>	See specified Test Circuit.	10			ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	"	13			ns
Fall Time	t <sub>f</sub>	"	70			ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -1A, V <sub>GS</sub> = 0	-0.9			V

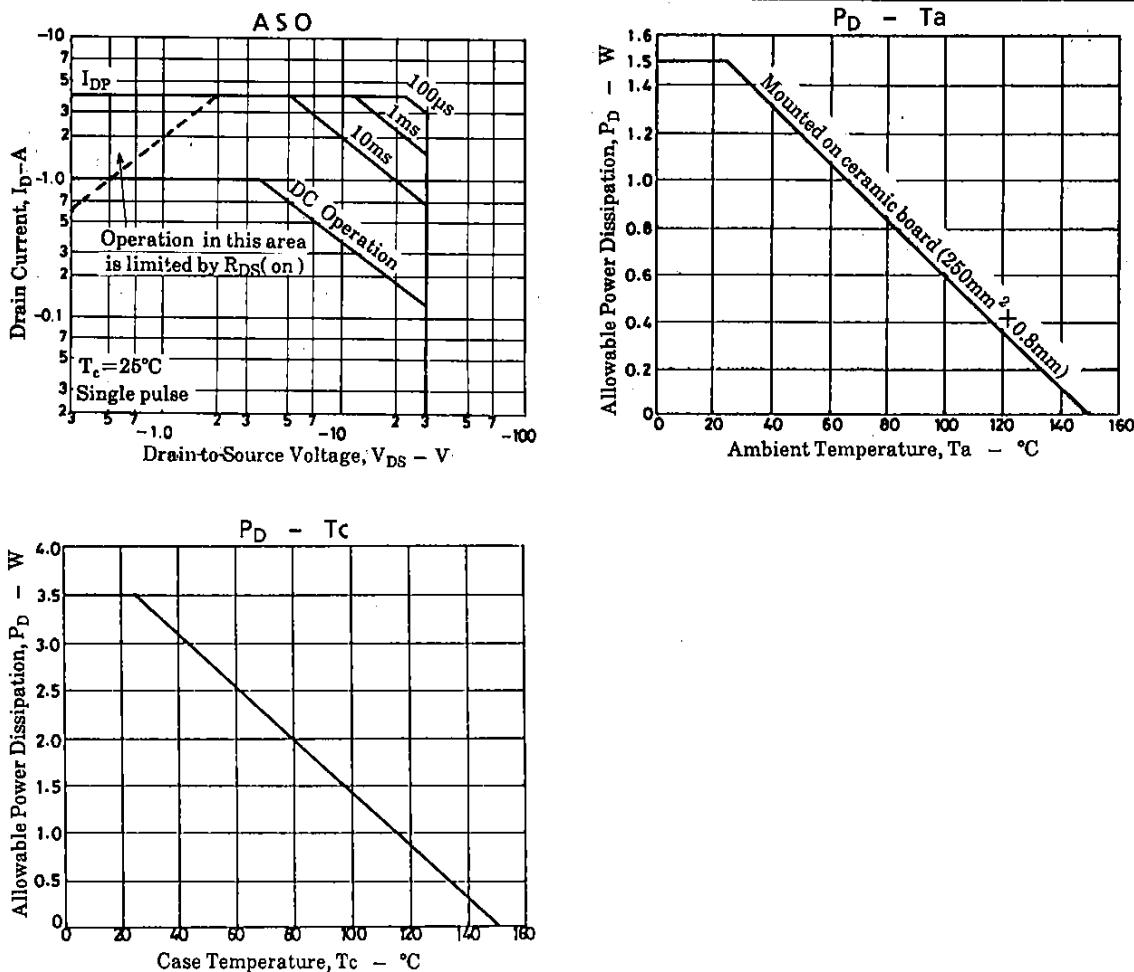
Marking : JA

**Switching Time Test Circuit****Package Dimensions 2062****SANYO Electric Co., Ltd. Semiconductor Business Headquarters**

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